National Semiconductor

CD4512BM/CD4512BC 8-Channel Buffered Data Selector

General Description

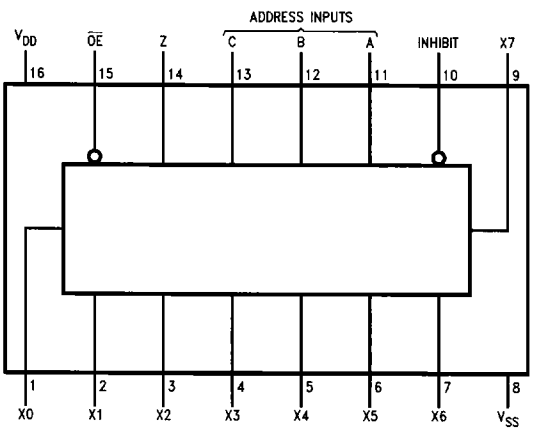
The CD4512BM/CD4512BC buffered 8-channel data selector is a complementary MOS (CMOS) circuit constructed with N- and P-channel enhancement mode transistors. This data selector is primarily used as a digital signal multiplexer selecting 1 of 8 inputs and routing the signal to a TRI-STATE® output. A high level at the Inhibit input forces a low level at the output. A high level at the Output Enable ($\overline{OE}$) input forces the output into the TRI-STATE condition. Low levels at both the Inhibit and ($\overline{OE}$) inputs allow normal operation.

Features

- Wide supply voltage range 3.0V to 15V
- High noise immunity 0.45 V_{DD} (typ.)
- TRI-STATE output
- Low quiescent power dissipation 0.25 μW/package (typ.) @ V_{CC} = 5.0V
- Plug-in replacement for Motorola MC14512

Connection Diagram and Truth Table

Dual-In-Line Package



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Top View

Order Number CD4512B*

*Please look into Section 8, Appendix D for availability of various package types.

Address Inputs			Control Inputs		Output
C	B	A	Inhibit	$\overline{OE}$	Z
0	0	0	0	0	X0
0	0	1	0	0	X1
0	1	0	0	0	X2
0	1	1	0	0	X3
1	0	0	0	0	X4
1	0	1	0	0	X5
1	1	0	0	0	X6
1	1	1	0	0	X7
ⓘ	ⓘ	ⓘ	1	0	0
ⓘ	ⓘ	ⓘ	ⓘ	1	Hi-Z

ⓘ = Don't care

Hi-Z = TRI-STATE condition

Xn = Data at input n

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Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V_{DD})	-0.5 to $+18$ V_{DC}
Input Voltage (V_{IN})	-0.5 to $V_{DD} + 0.5$ V_{DC}
Storage Temperature Range (T_S)	$-65°C$ to $+150°C$
Power Dissipation (P_D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature, (T_L) (Soldering, 10 seconds)	260°C

Recommended Operating Conditions (Note 2)

DC Supply Voltage (V_{DD})	3.0 to 15 V_{DC}
Input Voltage (V_{IN})	0 to V_{DD} V_{DC}
Operating Temperature Range (T_A)	
CD4512BM	$-55°C$ to $+125°C$
CD4512BC	$-40°C$ to $+85°C$

DC Electrical Characteristics CD4512BM (Note 2)

Symbol	Parameter	Conditions	−55°C		+25°C			+125°C		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5V, V_{IN} = V_{DD}$ or V_{SS}		5.0		0.005	5.0		150	μA
		$V_{DD} = 10V, V_{IN} = V_{DD}$ or V_{SS}		10		0.010	10		300	μA
		$V_{DD} = 15V, V_{IN} = V_{DD}$ or V_{SS}		20		0.015	20		600	μA
V_{OL}	Low Level Output Voltage	$V_{DD} = 5V$ } $\lvert I_{OL}\rvert < 1$ μA		0.05		0	0.05		0.05	V
		$V_{DD} = 10V$ }		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$ }		0.05		0	0.05		0.05	V
V_{OH}	High Level Output Voltage	$V_{DD} = 5V$ } $\lvert I_{OH}\rvert < 1$ μA	4.95		4.95	5.0		4.95		V
		$V_{DD} = 10V$ }	9.95		9.95	10.0		9.95		V
		$V_{DD} = 15V$ }	14.95		14.95	15.0		14.95		V
V_{IL}	Low Level Input Voltage	$V_{DD} = 5V, V_O = 0.5V$		1.5		2.25	1.5		1.5	V
		$V_{DD} = 10V, V_O = 1.0V$		3.0		4.50	3.0		3.0	V
		$V_{DD} = 15V, V_O = 1.5V$		4.0		6.75	4.0		4.0	V
V_{IH}	High Level Input Voltage	$V_{DD} = 5V, V_O = 4.5V$	3.5		3.5	2.75		3.5		V
		$V_{DD} = 10V, V_O = 9.0V$	7.0		7.0	5.50		7.0		V
		$V_{DD} = 15V, V_O = 13.5V$	11.0		11.0	8.25		11.0		V
I_{OL}	Low Level Output Current (Note 3)	$V_{DD} = 5V, V_O = 0.4V$	0.64		0.51	0.78		0.36		mA
		$V_{DD} = 10V, V_O = 0.5V$	1.6		1.3	2.0		0.9		mA
		$V_{DD} = 15V, V_O = 1.5V$	4.2		3.4	7.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	$V_{DD} = 5V, V_O = 4.6V$	−0.25		−0.2			−0.14		mA
		$V_{DD} = 10V, V_O = 9.5V$	−0.62		−0.5			−0.35		mA
		$V_{DD} = 15V, V_O = 13.5V$	−1.8		−1.5			−1.1		mA
I_{IN}	Input Current	$V_{DD} = 15V, V_{IN} = 0V$		−0.1		-10^{-5}	−0.1		−1.0	μA
		$V_{DD} = 15V, V_{IN} = 15V$		0.1		10^{-5}	0.1		1.0	μA
I_{OZ}	TRI-STATE Output Current	$V_{DD} = 15V, V_O = 0V$		±0.1		-10^{-5}	±0.1		±3.0	μA
		$V_{DD} = 15V, V_O = 15V$								

DC Electrical Characteristics CD4512BC (Note 2)

Symbol	Parameter	Conditions	−40°C		+25°C			+85°C		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5V, V_{IN} = V_{DD}$ or V_{SS}		20		0.005	20		150	μA
		$V_{DD} = 10V, V_{IN} = V_{DD}$ or V_{SS}		40		0.010	40		300	μA
		$V_{DD} = 15V, V_{IN} = V_{DD}$ or V_{SS}		80		0.015	80		600	μA
V_{OL}	Low Level Output Voltage	$V_{DD} = 5V$ } $\lvert I_{OL}\rvert < 1$ μA		0.05		0	0.05		0.05	V
		$V_{DD} = 10V$ }		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$ }		0.05		0	0.05		0.05	V
V_{OH}	High Level Output Voltage	$V_{DD} = 5V$ } $\lvert I_{OH}\rvert < 1$ μA	4.95		4.95	5.0		4.95		V
		$V_{DD} = 10V$ }	9.95		9.95	10.0		9.95		V
		$V_{DD} = 15V$ }	14.95		14.95	15.0		14.95		V
V_{IL}	Low Level Input Voltage	$V_{DD} = 5V, V_O = 0.5V$		1.5		2.25	1.5		1.5	V
		$V_{DD} = 10V, V_O = 1.0V$		3.0		4.50	3.0		3.0	V
		$V_{DD} = 15V, V_O = 1.5V$		4.0		6.75	4.0		4.0	V

DC Electrical Characteristics CD4512BC (Note 2) (Continued)

Symbol	Parameter	Conditions	−40°C		+25°C			+85°C		Units
			Min	Max	Min	Typ	Max	Min	Max	
V_{IH}	High Level Input Voltage	V_{DD} = 5V, V_O = 4.5V	3.5		3.5	2.75		3.5		V
		V_{DD} = 10V, V_O = 9.0V	7.0		7.0	5.50		7.0		V
		V_{DD} = 15V, V_O = 13.5V	11.0		11.0	8.25		11.0		V
I_{OL}	Low Level Output Current (Note 3)	V_{DD} = 5V, V_O = 0.4V	0.52		0.44	0.78		0.36		mA
		V_{DD} = 10V, V_O = 0.5V	1.3		1.1	2.0		0.9		mA
		V_{DD} = 15V, V_O = 1.5V	3.6		3.4	7.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	V_{DD} = 5V, V_O = 4.6V	−0.2		−0.16			−0.12		mA
		V_{DD} = 10V, V_O = 9.5	−0.5		−0.4			−0.3		mA
		V_{DD} = 15V, V_O = 13.5V	−1.4		−1.2			−1.0		mA
I_{IN}	Input Current	V_{DD} = 15V, V_{IN} = 0V		−0.3		-10^{-5}	−0.3		−1.0	μA
		V_{DD} = 15V, V_{IN} = 15V		0.3		10^{-5}	0.3		1.0	μA
I_{OZ}	TRI-STATE Output Current	V_{DD} = 15V, V_O = 0V		±1.0		$\pm10^{-5}$	±1.0		±7.5	μA
		V_{DD} = 15V, V_O = 15V								

AC Electrical Characteristics* T_A = 25°C, t_r = t_f = 20 ns, C_L = 50 pF

Symbol	Parameter	Conditions	CD4512BM			CD4512BC			Units
			Min	Typ	Max	Min	Typ	Max	
t_{PHL}	Propagation Delay High-to-Low Level	V_{DD} = 5V		225	500		225	750	ns
		V_{DD} = 10V		75	175		75	200	ns
		V_{DD} = 15V		57	130		57	150	ns
t_{PLH}	Propagation Delay Low-to-High Level	V_{DD} = 5V		225	500		225	750	ns
		V_{DD} = 10V		75	175		75	200	ns
		V_{DD} = 15V		57	130		57	150	ns
t_{THL}, t_{TLH}	Transition Time	V_{DD} = 5V		70	200		70	200	ns
		V_{DD} = 10V		35	100		35	100	ns
		V_{DD} = 15V		25	80		25	80	ns
t_{PHZ}, t_{PLZ}	Propagation Delay into TRI-STATE from Logic Level	V_{DD} = 5V		50	125		50	125	ns
		V_{DD} = 10V		25	75		25	75	ns
		V_{DD} = 15V		19	60		19	60	ns
t_{PZH}, t_{PZL}	Propagation Delay to Logic Level from TRI-STATE	V_{DD} = 5V		50	125		50	125	ns
		V_{DD} = 10V		25	75		25	75	ns
		V_{DD} = 15V		19	60		19	60	ns
C_{IN}	Input Capacitance	(Note 4)		7.5	15		7.5	15	pF
C_{OUT}	TRI-STATE Output Capacitance	(Note 4)		7.5	15		7.5	15	pF
C_{PD}	Power Dissipation Capacity	(Note 5)		150			150		pF

*AC Parameters are guaranteed by DC correlated testing.

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Recommended Operating Conditions" and "Electrical Characteristics" provide conditions for actual device operation.

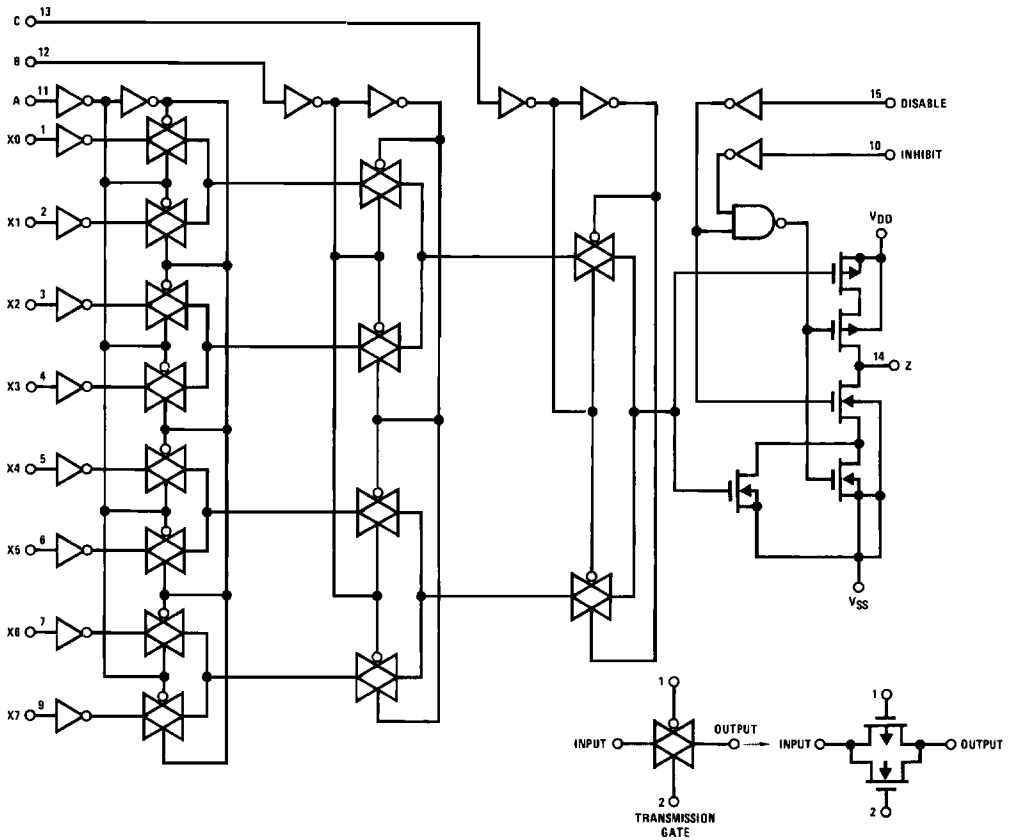
Note 2: V_{SS} = 0V unless otherwise specified.

Note 3: I_{OH} and I_{OL} are tested one output at a time.

Note 4: Capacitance guaranteed by periodic testing.

Note 5: C_{PD} determines the no load AC power of any CMOS device. For complete explanation, see 54C/74C Family Characteristics Application Note, AN-90.

Logic Diagram



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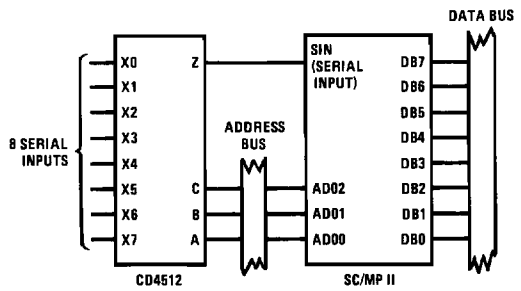
Typical Application

Serial Data Routing Interface



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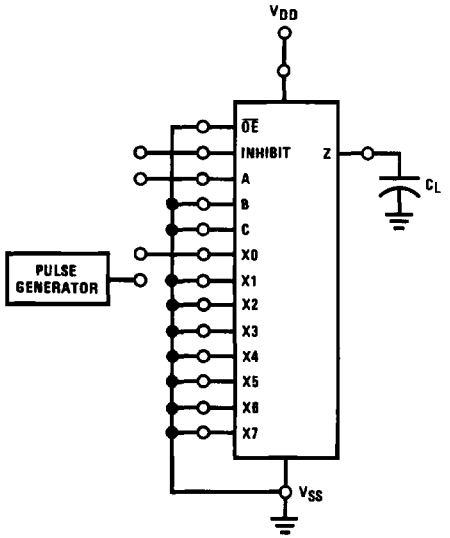
AC Test Circuit and Switching Time Waveforms



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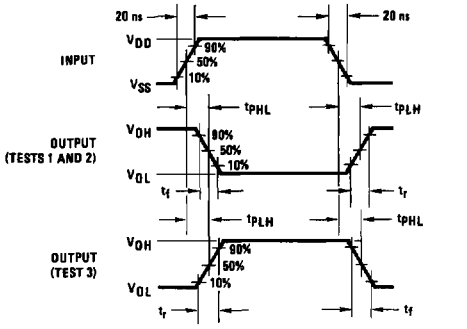

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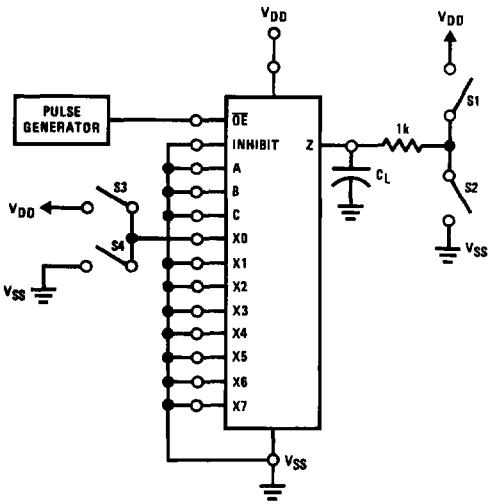
Input Connections for t_r, t_f, t_{PLH}, t_{PHL}

Test	Inhibit	A	X0
1	PG	GND	V_{DD}
2	GND	PG	V_{DD}
3	GND	GND	PG

TRI-STATE AC Test Circuit and Switching Time Waveforms



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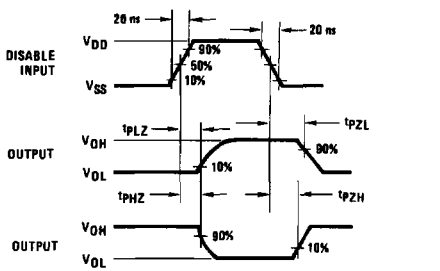

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Switch Positions for TRI-STATE Test

Test	S1	S2	S3	S4
t_{PHZ}	Open	Closed	Closed	Open
t_{PLZ}	Closed	Open	Open	Closed
t_{PZL}	Closed	Open	Open	Closed
t_{PZH}	Open	Closed	Closed	Open

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